Complementary Power Transistors

DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain-Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CB}	70	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current	I _C	10	Adc
Base Current	I _B	6	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D [†]	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T _A = 25°C Derate above 25°C	P _D	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C
ESD - Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

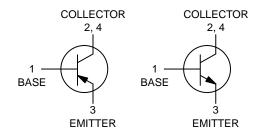


ON Semiconductor®

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SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

COMPLEMENTARY





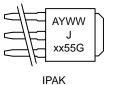


DPAK CASE 369C STYLE 1

IPAK CASE 369D STYLE 1

MARKING DIAGRAMS





DPAK

G

A = Assembly Location

Y = Year WW = Work Week Jxx55 = Device Code x = 29 or 30

ORDERING INFORMATION

= Pb-Free Package

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

[†]Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	71.4	°C/W

^{2.} These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-		•	*
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 30 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	60	_	Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0)	I _{CEO}	-	50	μAdc
Collector Cutoff Current $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 70 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	I _{CEX}	- -	0.02 2	mAdc
Collector Cutoff Current $(V_{CB} = 70 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 70 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	Ісво	- -	0.02 2	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)	I _{EBO}	-	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) ($I_C = 4$ Adc, $V_{CE} = 4$ Vdc) ($I_C = 10$ Adc, $V_{CE} = 4$ Vdc)	h _{FE}	20 5	100	_
Collector–Emitter Saturation Voltage (Note 3) $(I_C = 4 \text{ Adc}, I_B = 0.4 \text{ Adc})$ $(I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc})$	V _{CE(sat)}	- -	1.1 8	Vdc
Base–Emitter On Voltage (Note 3) (I _C = 4 Adc, V _{CE} = 4 Vdc)	V _{BE(on)}	-	1.8	Vdc
DYNAMIC CHARACTERISTICS			•	•
Current–Gain – Bandwidth Product (I _C = 500 mAdc, V _{CE} = 10 Vdc, f = 500 kHz)	f _T	2	_	MHz
Pulsa Tast: Pulsa Width < 300 us Duty Cycla < 2%	•		•	+

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

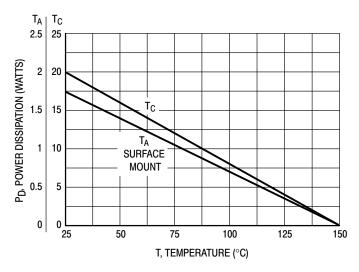


Figure 1. Power Derating

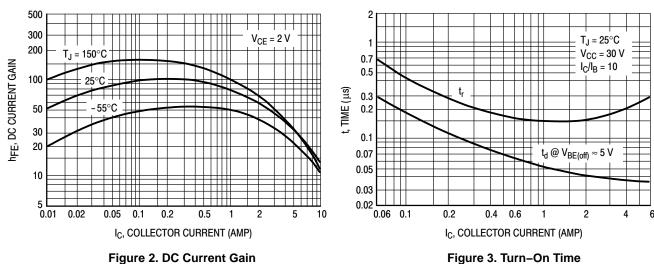


Figure 2. DC Current Gain

V, VOLTAGE (VOLTS)

1.4 $T_J = 25^{\circ}C$ 3 V_{CC} = 30 V 1.2 $T_J = 25^{\circ}C$ 2 $I_C/I_B = 10$ $I_{B1} = I_{B2}$ t, TIME (µs) 8.0 $V_{BE(sat)} @ I_C/I_B = 10$ 0.7 0.5 0.6 V_{BE} @ V_{CE} = 2 V 0.3 0.2 $t_{\rm f}$ 0.4 0.1 0.2 $V_{CE(sat)} @ I_C/I_B = 10$ 0.07 0 l 10 0.06 0.1 0.6 0.1 0.2 0.3 I_C, COLLECTOR CURRENT (AMP) I_C, COLLECTOR CURRENT (AMP)

Figure 4. "On" Voltages, MJD3055

Figure 5. Turn-Off Time

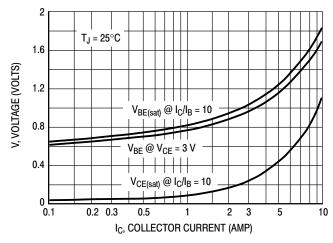
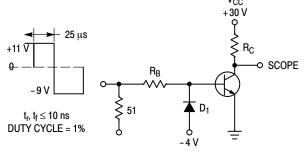


Figure 6. "On" Voltages, MJD2955



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS $D_1 \ \text{MUST BE FAST RECOVERY TYPE, eg:} \\ 1N5825 \ \text{USED ABOVE I}_B \approx 100 \ \text{mA} \\ \text{MSD6100 USED BELOW I}_B \approx 100 \ \text{mA}$

Figure 7. Switching Time Test Circuit

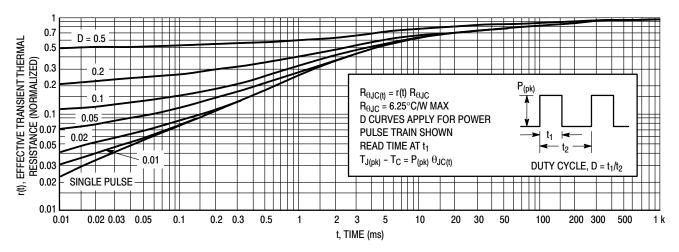


Figure 8. Thermal Response

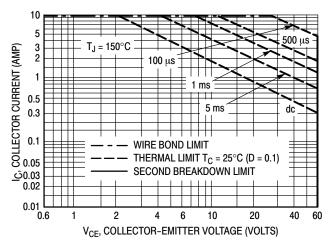


Figure 9. Maximum Forward Bias Safe Operating Area

Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150^{\circ} C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ} C$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

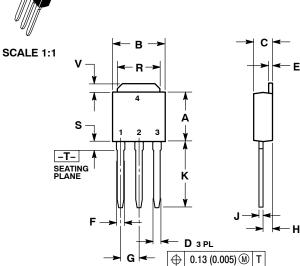
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

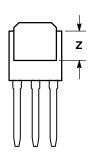
MECHANICAL CASE OUTLINE





DATE 15 DEC 2010





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETE	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

MARKING DIAGRAMS

STYLE 1:			
BASE			
COLLECTOR			
EMITTER			
COLLECTOR			
	BASE COLLECTOR EMITTER		

STYLE 5: PIN 1. GATE

2. ANODE CATHODE

ANODE

STYLE 2: PIN 1. GATE 2. DRAIN SOURCE 3 DRAIN

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

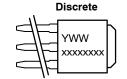
MT2

STYLE 3: PIN 1. ANODE 2. CATHODE 3 ANODE 4. CATHODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER COLLECTOR STYLE 4: PIN 1. CATHODE ANODE
 GATE

4. ANODE



WW



xxxxxxxxx = Device Code Α = Assembly Location IL = Wafer Lot Υ = Year

= Work Week

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A1

DETAIL A ROTATED 90° CW

DPAK (SINGLE GAUGE) CASE 369C

BOTTOM VIEW

ALTERNATE CONSTRUCTIONS

DATE 21 JUL 2015

- IOTES. 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

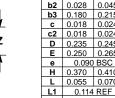
- MENSIONS b3, L3 and Z.

 Jimensions b And E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

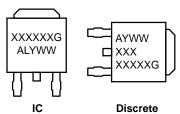
 MENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	



GENERIC MARKING DIAGRAM*

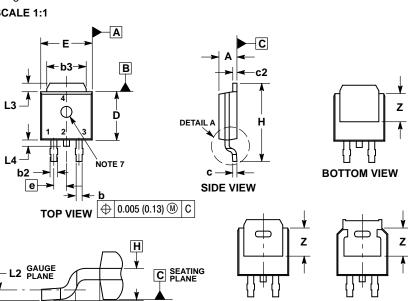


XXXXXX = Device Code

= Assembly Location Α = Wafer Lot L Υ = Year = Work Week WW G = Pb-Free Package

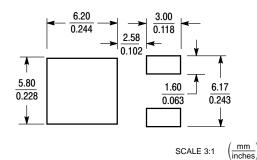
*This information is generic. Please refer to device data sheet for actual part marking.

ISSUE F



STYLE 1: PIN 1. BASE 2. COLLE 3. EMITTI 4. COLLE	ER 3.		STYLE 3: PIN 1. ANODI 2. CATHO 3. ANODI 4. CATHO	E DDE E	TYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLEC 3. EMITTER 4. COLLEC	TOR 2	E 8: 1. N/C 2. CATHODE 3. ANODE 4. CATHODE	3. F		STYLE 10: PIN 1. CATHODE 2. ANODE T 3. CATHODE 4. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DPAK SINGLE GAUGE SURFACE MOUNT		PAGE 1 OF 2	



DOCUMENT	NUMBER:
98AON10527	7D

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY L. GAN	24 SEP 2001
А	ADDED STYLE 8. REQ. BY S. ALLEN.	06 AUG 2008
В	ADDED STYLE 9. REQ. BY D. WARNER.	16 JAN 2009
С	ADDED STYLE 10. REQ. BY S. ALLEN.	09 JUN 2009
D	RELABELED DRAWING TO JEDEC STANDARDS. ADDED SIDE VIEW DETAIL A. CORRECTED MARKING INFORMATION. REQ. BY D. TRUHITTE.	29 JUN 2010
E	ADDED ALTERNATE CONSTRUCTION BOTTOM VIEW. MODIFIED DIMENSIONS b2 AND L1. CORRECTED MARKING DIAGRAM FOR DISCRETE. REQ. BY I. CAMBALIZA.	06 FEB 2014
F	ADDED SECOND ALTERNATE CONSTRUCTION BOTTOM VIEW. REQ. BY K. MUSTAFA.	21 JUL 2015

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